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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	8.4 6.8	A
	t<10s	T_A = +25°C T_A = +70°C	I_D	11.0 9.0	A
Maximum Body Diode Forward Current (Note 6)			I_S	2.5	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I_{DM}	80	A
Avalanche Current (Notes 7) L = 0.1mH			I_{AS}	22	A
Avalanche Energy (Notes 7) L = 0.1mH			E_{AS}	25	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	1.2	W
	T_A = +70°C		0.8	
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	$R_{\theta JA}$	102	°C/W
	t<10s		62	
Total Power Dissipation (Note 6)	T_A = +25°C	P_D	1.6	W
	T_A = +70°C		1.0	
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	$R_{\theta JA}$	78	°C/W
	t<10s		47	
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	14.5	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 30V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	1.3	—	2.5	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	8	15	mΩ	V_{GS} = 10V, I_D = 12A
		—	12	18		V_{GS} = 4.5V, I_D = 10A
Diode Forward Voltage	V_{SD}	—	0.7	1.0	V	V_{GS} = 0V, I_S = 1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	1415	—	pF	V_{DS} = 15V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	119	—		
Reverse Transfer Capacitance	C_{rss}	—	82	—		
Gate Resistance	R_G	—	2.6	3.2	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	11.3	—	nC	V_{DS} = 15V, I_D = 12A
Total Gate Charge (V_{GS} = 10V)	Q_g	—	25.1	—		
Gate-Source Charge	Q_{gs}	—	3.5	—		
Gate-Drain Charge	Q_{gd}	—	3.6	—		
Turn-On Delay Time	$t_{D(on)}$	—	4.8	—	nS	V_{DD} = 15V, V_{GS} = 10V, R_L = 1.25Ω, R_G = 3Ω,
Turn-On Rise Time	t_r	—	16.5	—		
Turn-Off Delay Time	$t_{D(off)}$	—	26.1	—		
Turn-Off Fall Time	t_f	—	5.6	—		
Body Diode Reverse Recovery Time	t_{rr}	—	8.5	—	nS	I_S = 12A, dI/dt = 500A/µs
Body Diode Reverse Recovery Charge	Q_{rr}	—	7.0	—	nC	I_S = 12A, dI/dt = 500A/µs

Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. UIS in production with L = 0.1mH, starting T_A = +25°C.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

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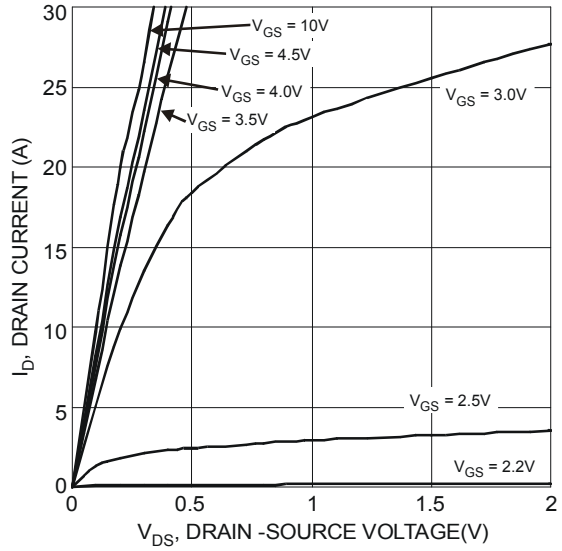

Figure 1 Typical Output Characteristics

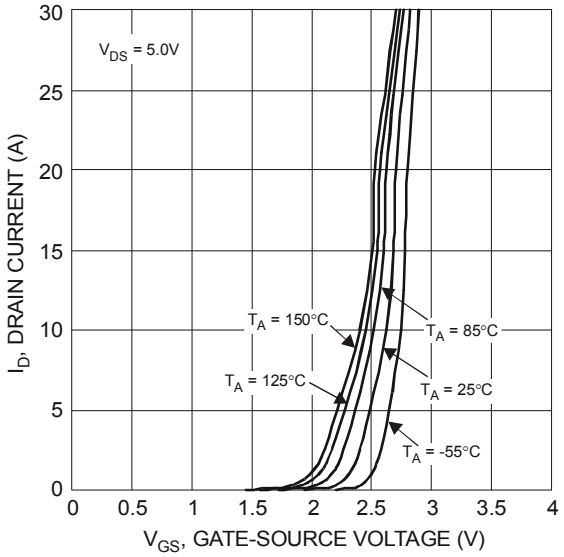

Figure 2 Typical Transfer Characteristics

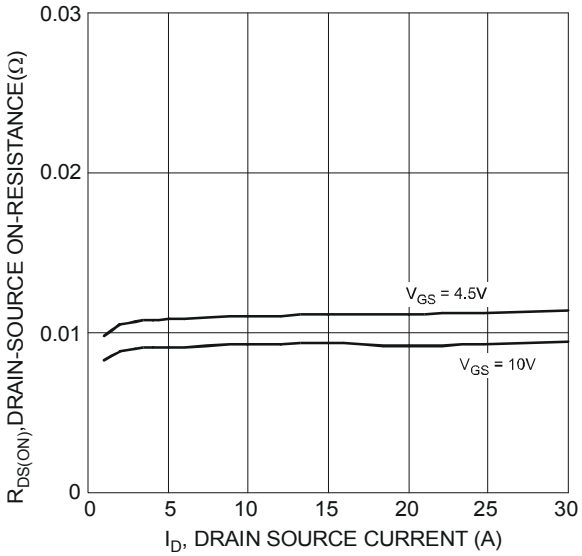

Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

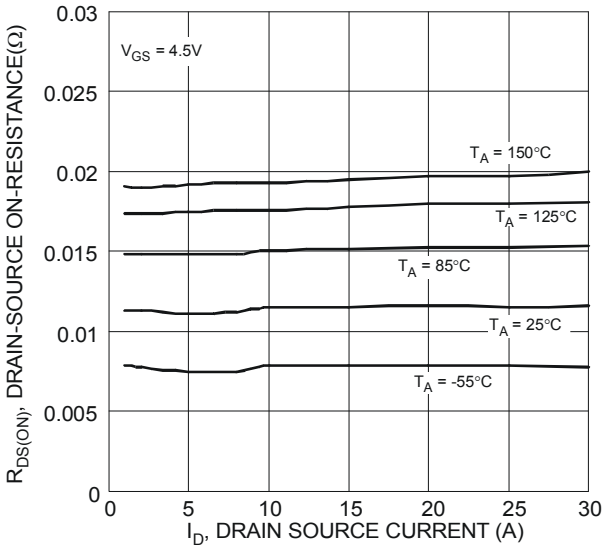

Figure 4 Typical On-Resistance vs. Drain Current and Temperature

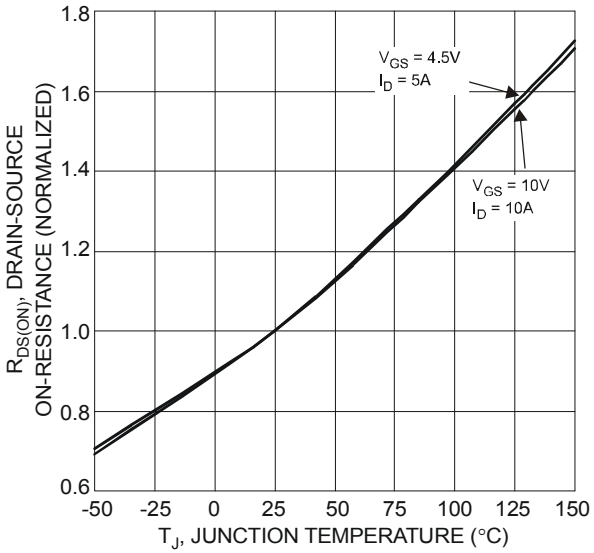

Figure 5 On-Resistance Variation with Temperature

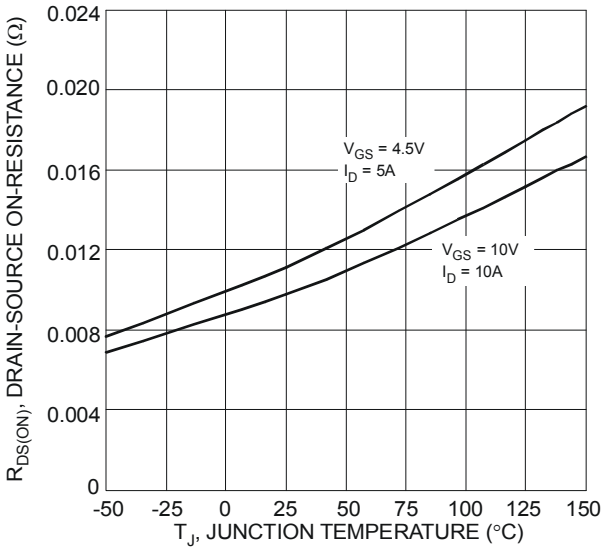

Figure 6 On-Resistance Variation with Temperature

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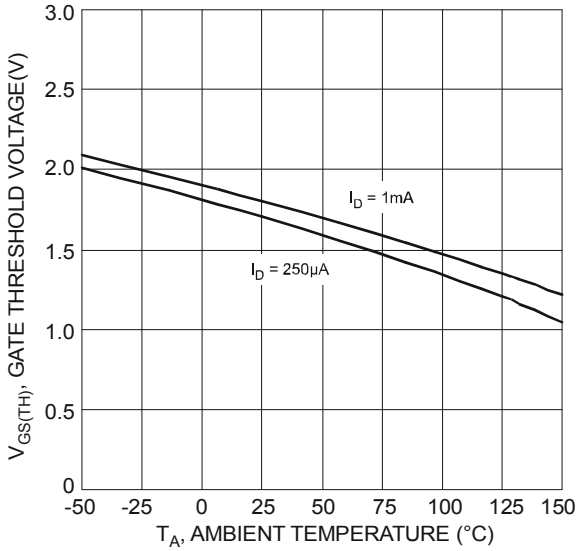

Figure 7 Gate Threshold Variation vs. Ambient Temperature

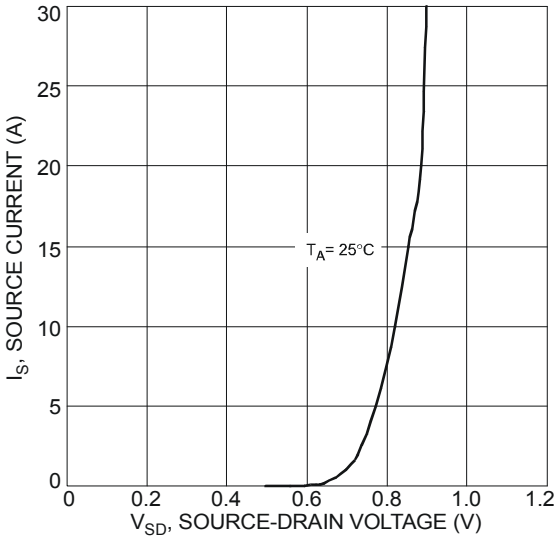

Figure 8 Diode Forward Voltage vs. Current

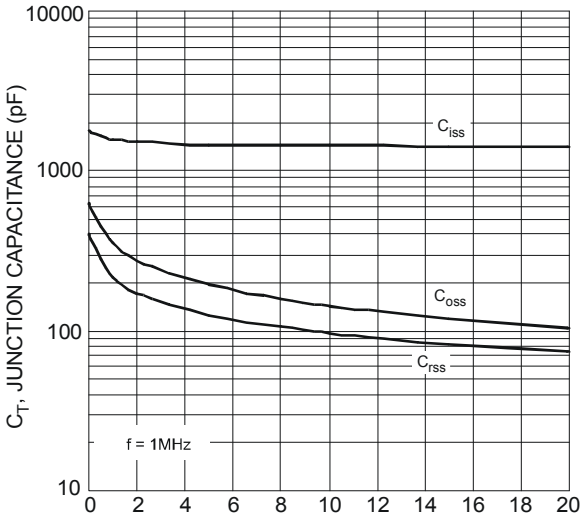

Figure 9 Typical Junction Capacitance

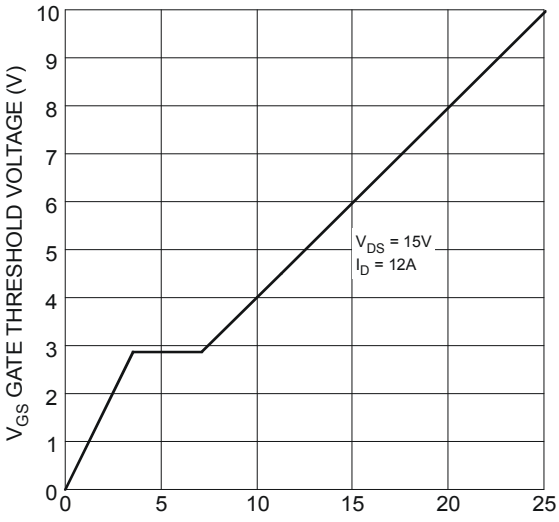

Figure 10 Gate Charge

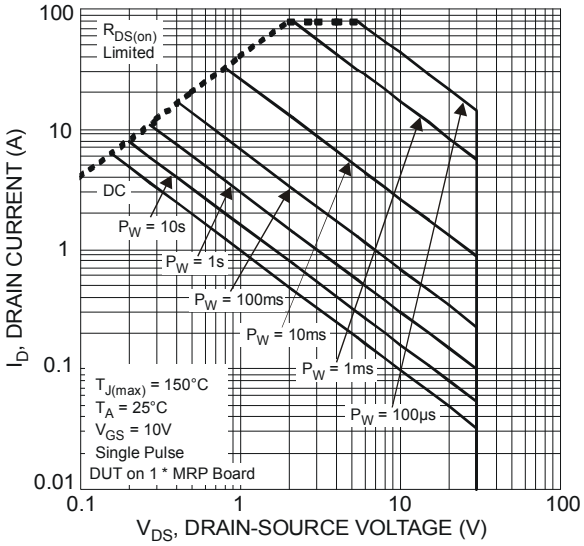

Figure 11 SOA, Safe Operation Area

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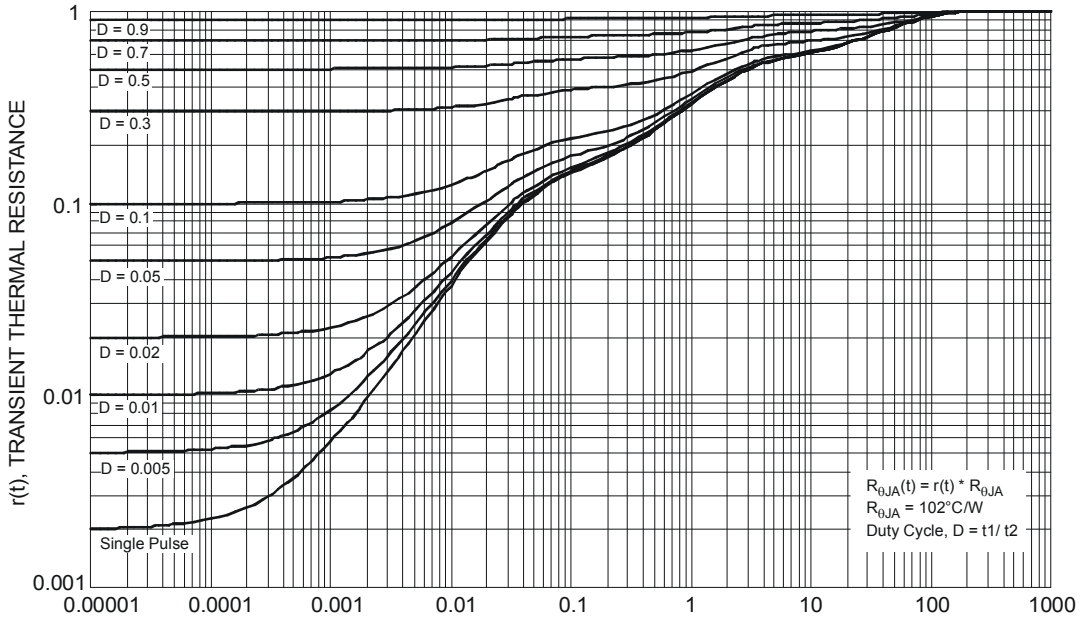
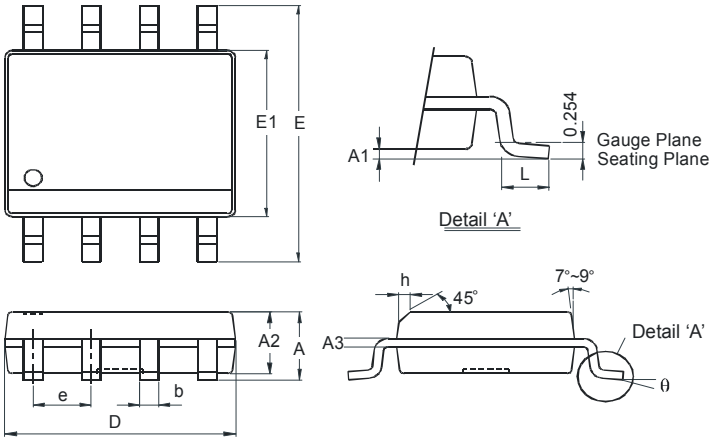


Figure 12 Transient Thermal Resistance

Package Outline Dimensions

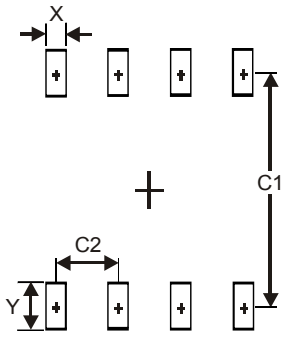
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SO-8		
Dim	**Min**	**Max**
A	-	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	-	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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